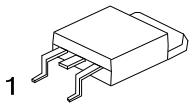
15N10

Power MOSFET

14.7A, 100V (D-S) N-CHANNEL POWER MOSFET



TO-252

■ DESCRIPTION

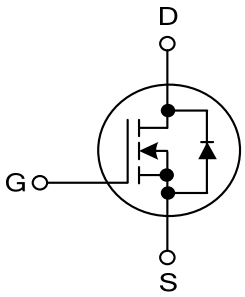
The UTC **15N10** is an N-Channel enhancement MOSFET, it uses UTC's advanced technology to provide customers with a minimum on-state resistance, high switching speed and low gate charge.

The UTC **15N10** is suitable for high efficiency switching DC/DC converter, LCD display inverter and load switch.

■ FEATURES

* $R_{DS(ON)}$=0.08Ω @V_{GS}=10V,I_D=8A
* Low gate charge (Typ=24nC)
* Low C_{RSS} (Typ=23pF)
* High switching speed

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
15N10L-TN3-T	15N10G-TN3-T	TO-252	G	D	S	Tube
15N10L-TN3-R	15N10G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

15N10L-TN3-R (1)Packing Type (2)Package Type (3)Lead Free	(1) T: Tube, R: Tape Reel (2) TN3: TO-252 (3) L: Lead Free, G: Halogen Free

■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise noted)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain-Source Voltage			V_{DSS}	100	V
Gate-Source Voltage			V_{GSS}	±20	V
Drain Current	Continuous	T_C=25°C, T_J=150°C	I_D	14.7	A
		T_C=70°C, T_J=150°C		13.6	A
	Pulsed		I_{DM}	59	A
Power Dissipation		T_C=25°C	P_D	34.7	W
		T_C=70°C		22.2	W
Operating Junction Temperature			T_J	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS (T_A=25°C, unless otherwise noted)

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case (Note)	θ_{JC}	3.6	°C/W

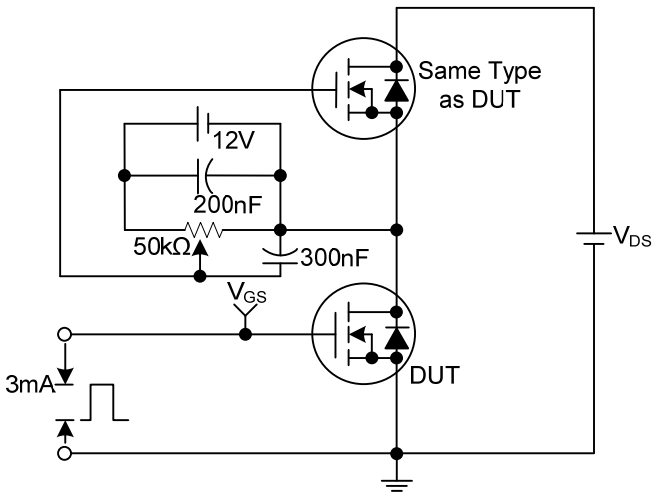
Note: The device mounted on 1in^2 FR4 board with 2 oz copper.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

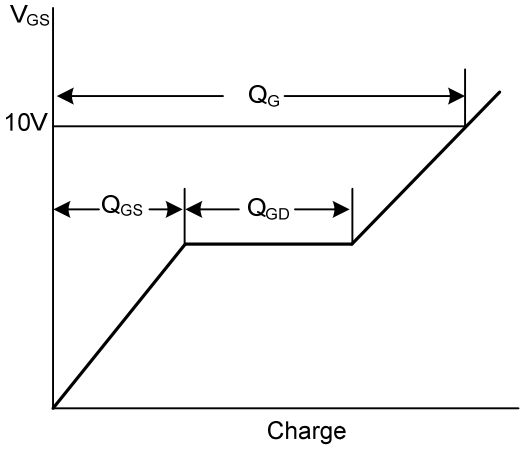
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=250μA, V_{GS}=0V	100			V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=80V, V_{GS}=0V			1	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=+20V, V_{DS}=0V			+100	nA
		V_{GS}=-20V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	1		3	V
Drain-Source On-State Resistance (Note)	$R_{DS(ON)}$	V_{GS}=10V, I_D=8A		80	100	mΩ
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	V_{GS}=0V, V_{DS}=15V, f=1MHz		890		pF
Output Capacitance	C_{OSS}			58		pF
Reverse Transfer Capacitance	C_{RSS}			23		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	V_{GS}=10V, V_{DS}=80V, I_D=10A		24		nC
Total Gate Charge	Q_G	V_{GS}=4.5V, V_{DS}=80V, I_D=10A		13		nC
Gate to Source Charge	Q_{GS}			4.6		nC
Gate to Drain Charge	Q_{GD}			7.6		nC
Gate-Resistance	R_G	V_{DS}=0V, V_{GS}=0V, f=1MHz		0.9		Ω
Turn-ON Delay Time	$t_{D(ON)}$	V_{DS}=50V, R_L=5Ω, V_{GEN}=10V, R_G=1Ω		14		ns
Rise Time	t_R			33		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			39		ns
Fall-Time	t_F			5		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V_{SD}	I_S=8A, V_{GS}=0V		0.9	1.2	V

Note: Pulse test: pulse width≤300us, duty cycle≤2%, Guaranteed by design, not subject to production testing.

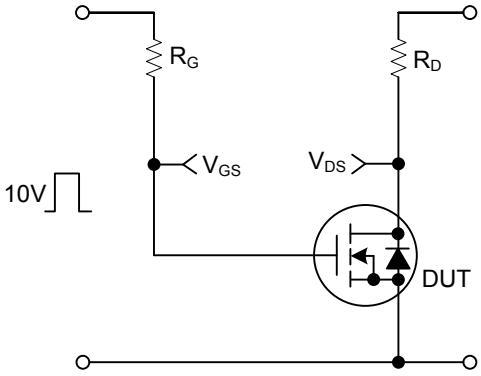
■ TEST CIRCUITS AND WAVEFORMS



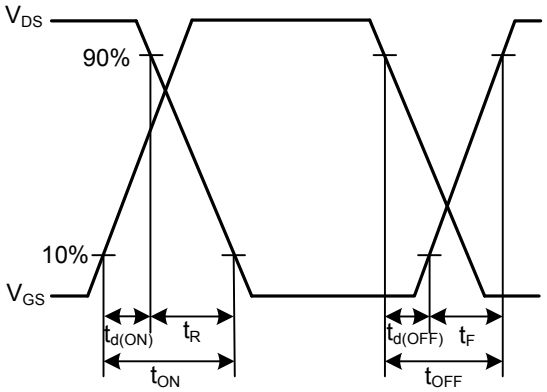
Gate Charge Test Circuit



Gate Charge Waveforms

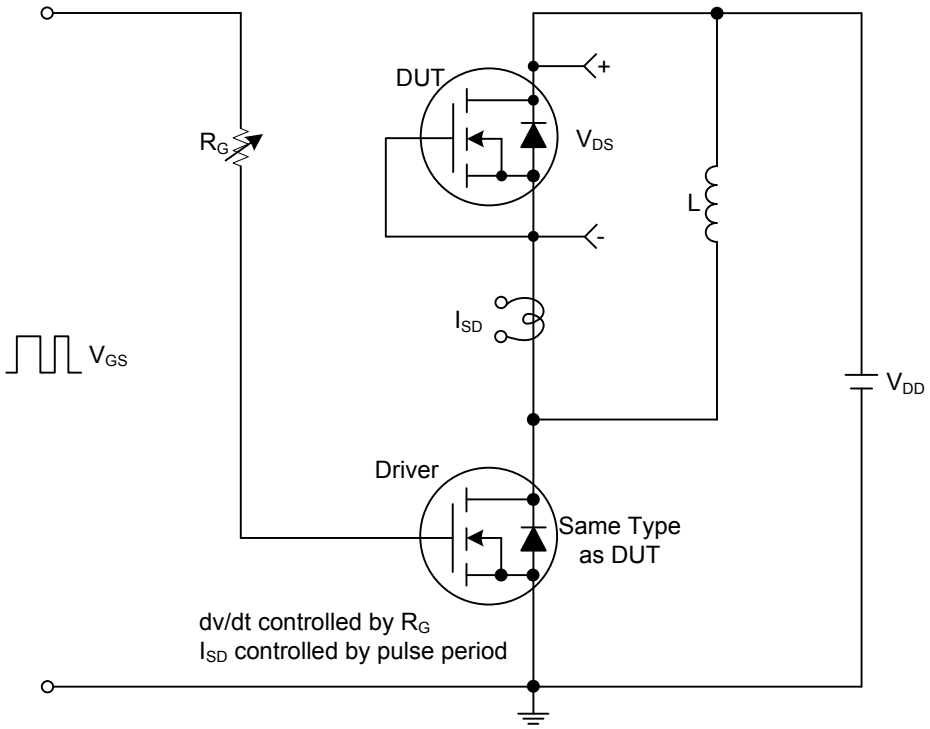


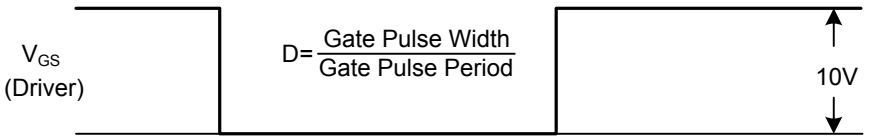
Resistive Switching Test Circuit

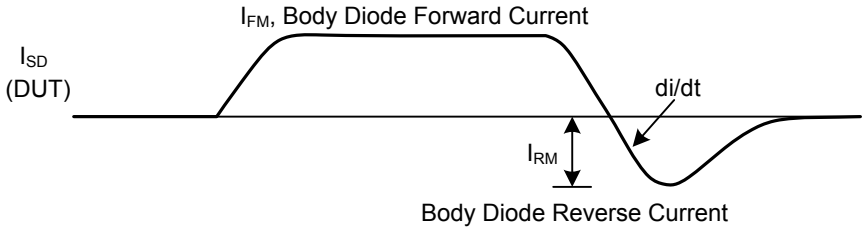


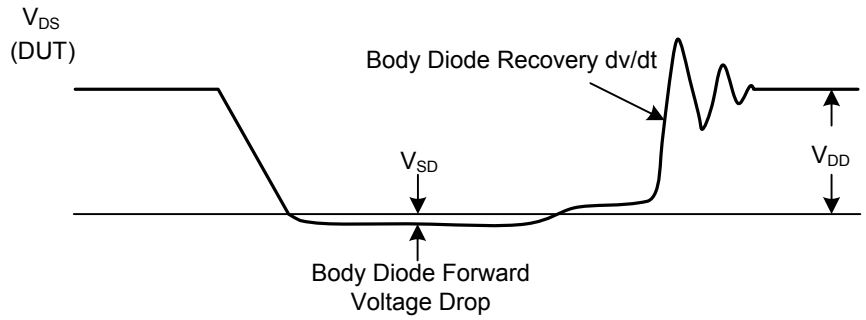
Resistive Switching Waveforms

■ TEST CIRCUITS AND WAVEFORMS





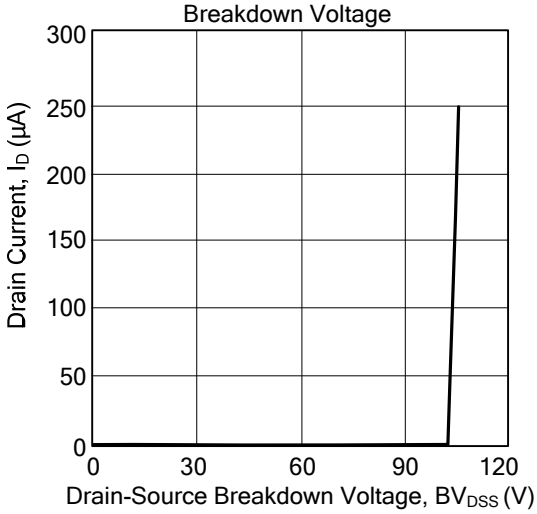




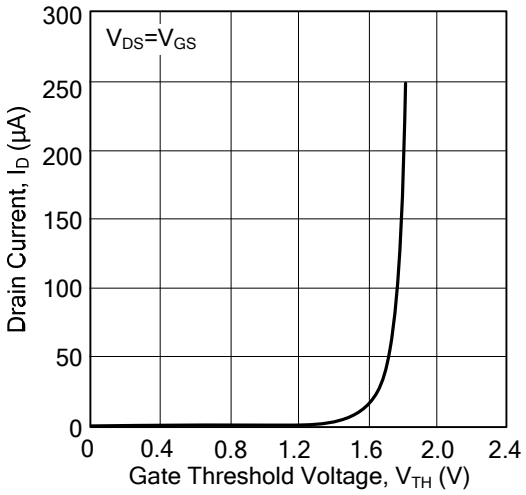
Peak Diode Recovery dv/dt Test Circuit and Waveforms

■ TYPICAL CHARACTERISTICS

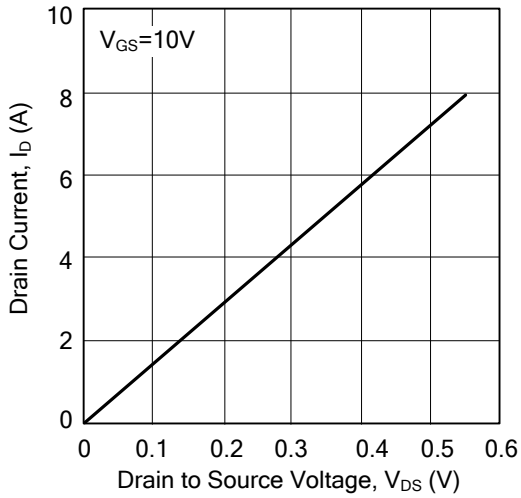
Drain Current vs. Drain-Source Breakdown Voltage



Drain Current vs. Gate Threshold Voltage



Drain-Source On-State Resistance Characteristics



Drain Current vs. Source to Drain Voltage